

Supporting Information

Methylamine lead bromide perovskite/protonated graphitic carbon nitride nanocomposites: interfacial charge carrier dynamics and photocatalysis

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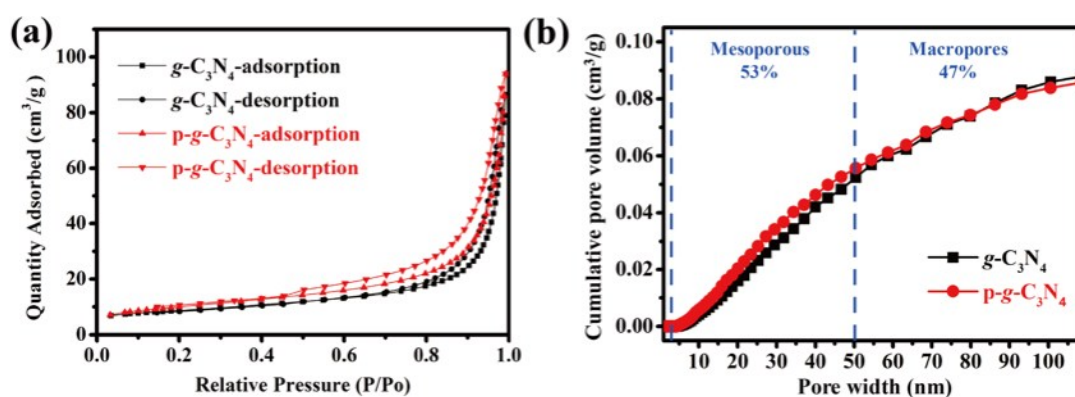


Fig. S1 (a) Nitrogen adsorption–desorption isotherms and (b) corresponding pore size distribution curves of $g\text{-C}_3\text{N}_4$ and $p\text{-}g\text{-C}_3\text{N}_4$.

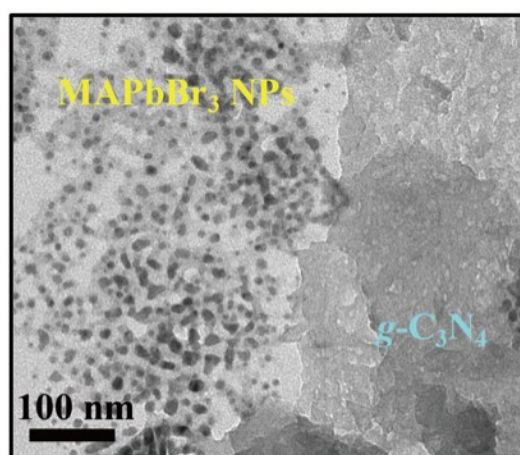


Fig. S2 TEM image of MAPbBr₃/g-C₃N₄ that was prepared by mixing g-C₃N₄ and precursors solution and then growth through the LARP process. The MAPbBr₃ NPs were observed around the edge and outside of g-C₃N₄ due to the weak interaction between g-C₃N₄ and precursor ions, MA⁺, Pb²⁺, and Br⁻.

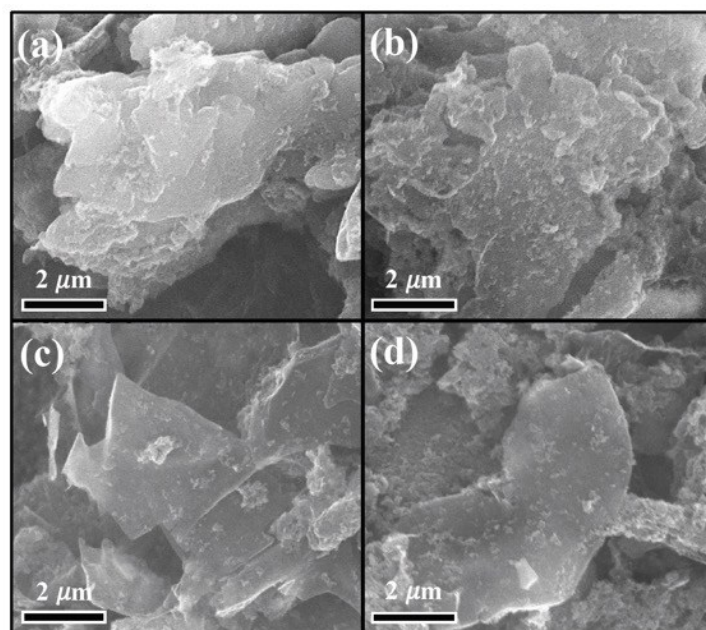


Fig. S3 SEM images of (a) p-g-C₃N₄, (b) MAPbBr₃/p-g-C₃N₄-0.25, (c) MAPbBr₃/p-g-C₃N₄-0.5, and (d) MAPbBr₃/p-g-C₃N₄-1.0. The significant decoration of MAPbBr₃ NPs on p-g-C₃N₄ can be observed. The decoration density of MAPbBr₃ NPs showed the progressively decrease as the loading amount of p-g-C₃N₄ increased.

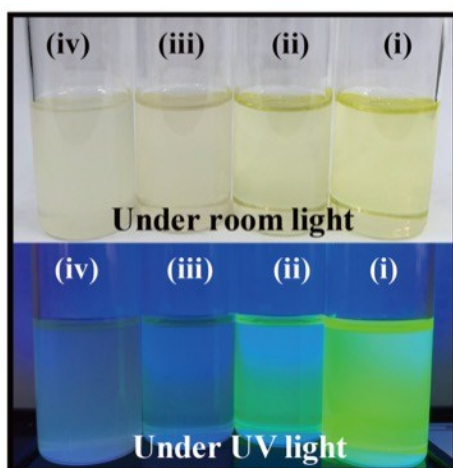


Fig. S4. Photograph of i. MAPbBr₃ NP and ii. MAPbBr₃/p-g-C₃N₄-0.25, iii. MAPbBr₃/p-g-C₃N₄-0.5, and iv. MAPbBr₃/p-g-C₃N₄-1.0 NCs solutions under room light and UV light (365 nm) irradiation. The progressively weaker PL emission of

MAPbBr₃ NPs when the incorporated amount of p-g-C₃N₄ was increased can be seen. Note that the concentration of MAPbBr₃ NPs in MAPbBr₃/ p-g-C₃N₄ NHS solutions was kept as a constant with the variation of loading amount of p-g-C₃N₄ to achieve the meaningful comparison of the PL intensity.

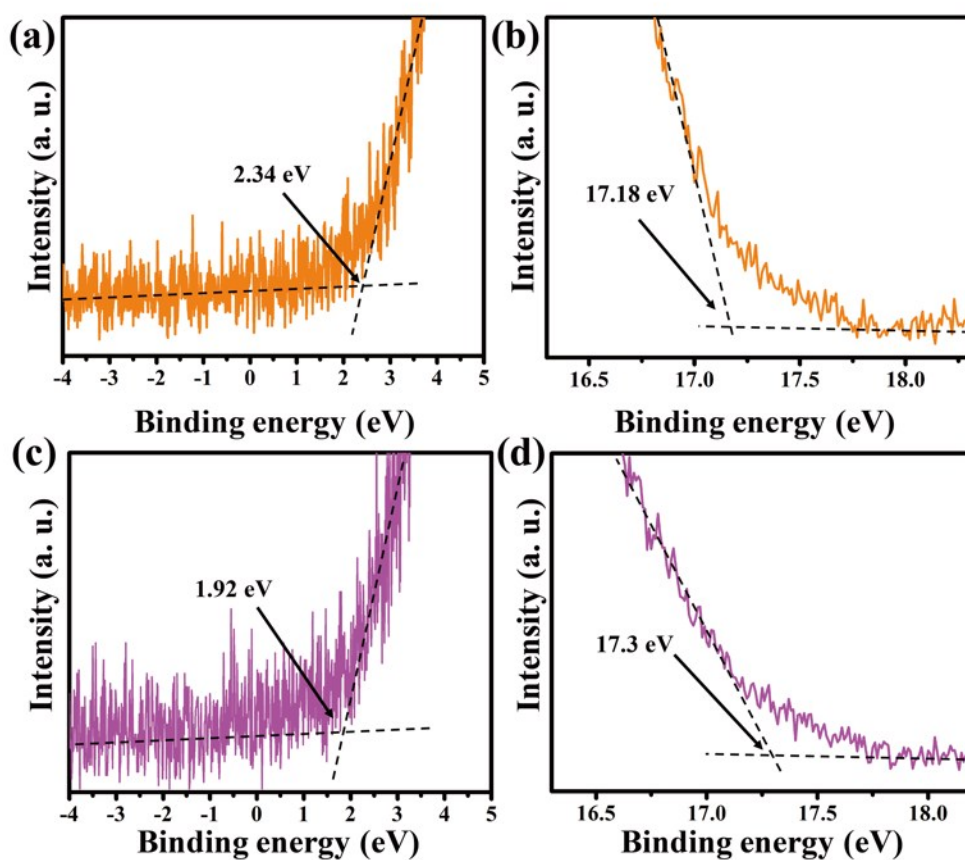


Fig. S5 UPS spectra as well as linear intersection for (a, b) p-g-C₃N₄ and (c, d) MAPbBr₃ NPs. The photoemission spectra were collected to zero point as the Fermi level, which revealed the secondary-electron cut-off energy as 17.18 and 17.3 eV for p-g-C₃N₄ and MAPbBr₃ NPs by linear extrapolation. The difference between the photon energy and the cut-off energy was calculated as the Fermi level (E_f) for the tested samples, giving -4.02 and -3.90 eV (vs. vacuum) for p-g-C₃N₄ and MAPbBr₃ NPs. On the other hand, the spectral feature close to the Fermi level represents the valence band structure of the tested samples. By the linear extrapolation along

the tangent of the spectrum onset, the valence band maximum (E_{vb}) with respect to the Fermi level ($E_{vb}-E_f$) can be obtained as 2.34 and 1.92 eV for p-g- C_3N_4 and MAPbBr₃ NPs. Therefore, the E_{vb} of p-g- C_3N_4 and MAPbBr₃ NPs can be determined as -6.36 and -5.82 eV (vs. vacuum). Furthermore, the conduction band minimum (E_{cb}) of the p-g- C_3N_4 and MAPbBr₃ NPs can be obtained by subtracting their optical band gap (E_g) values from E_{vb} , resulting in the E_{cb} as -3.66 and -3.43 eV (vs. vacuum), respectively.

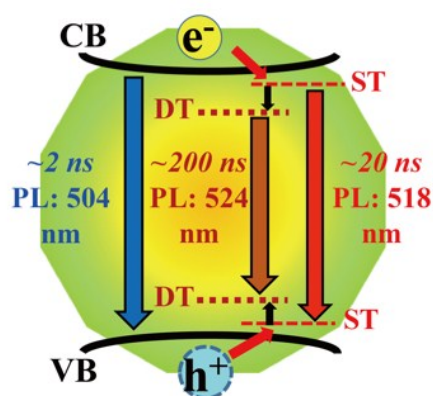


Fig. S6 Schematic illustration of the band structure and proposed assignment of lifetimes and rate constants of various charge carrier recombination and interfacial transfer processes for MAPbBr₃ NP. First, the photoexcited electron-hole pair in the CB and VB can be trapped into ST states and the further DT states in the time scale of ps. Second, the remained electrons and holes in the CB and VB can recombine through a radiative pathway on the time scale of 2 ns. Last, the trapped electrons and holes in ST and DT states can also recombine through radiative processes on the time scale of 20 and 200 ns, respectively.

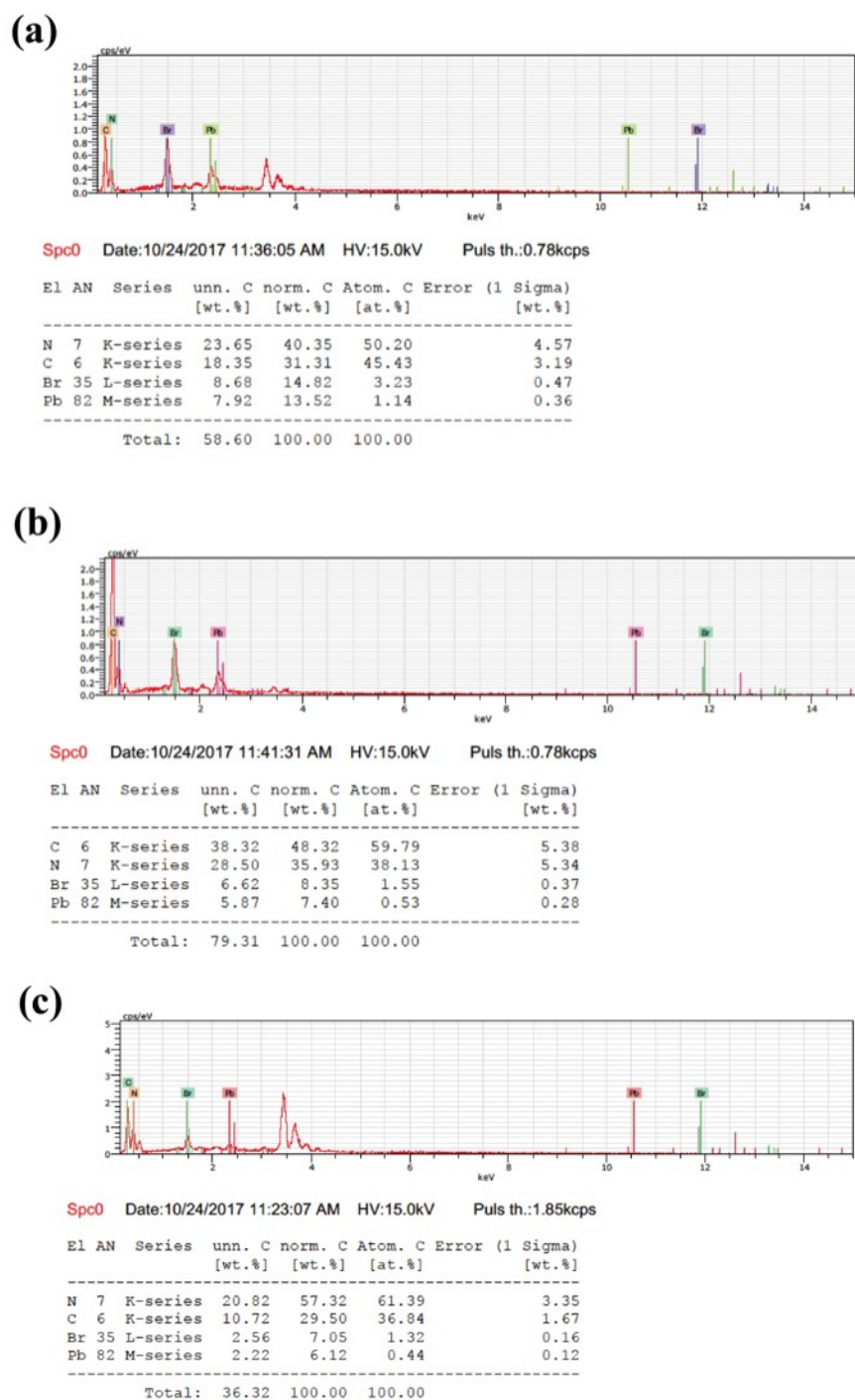


Fig. S7 SEM-EDS measurement results of (a) MAPbBr₃/p-g-C₃N₄-0.25, (b) MAPbBr₃/p-g-C₃N₄-0.5, and (c) MAPbBr₃/p-g-C₃N₄-1.0 NCs to identify their composition. Based on the wt.% values of Pb and Br and the formula, CH₃NH₃PbBr₃, we can quantitatively calculate the total wt.% of MAPbBr₃ in MAPbBr₃/p-g-C₃N₄ NCs. The constitutions of MAPbBr₃ were 30.24, 16.80 and 14.05 wt.% in the MAPbBr₃/p-g-C₃N₄-0.25, MAPbBr₃/p-g-C₃N₄-0.5, and MAPbBr₃/p-g-C₃N₄-1.0 NCs, respectively.